

1. Scope :

1-1. This specification applies to N channel depletion MOSFET chips,
Device no. PM-0307

2. Structure :

- 2-1. Planar type.
- 2-2. Electrodes.
Source : Aluminum alloy .
Gate : Aluminum alloy .
Drain : Gold alloy.

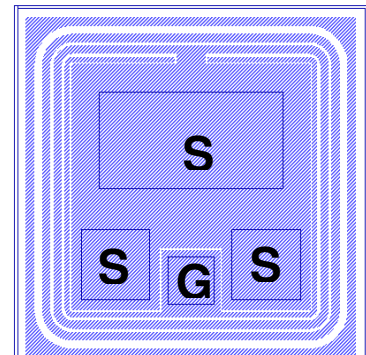
3. Size :

- 3-1. Chip size : 48 mils ×48 mils (1.220 mm ×1.220 mm).
- 3-2. Chip thickness : 12 ±1.5mils (0.305± 0.038mm).
- 3-3. Pad size :
Source : 25.1 mils × 12.8 mils (0.638 mm × 0.326mm).
Gate : 6.5 mils × 6.5 mils (0.164mm × 0.164 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Absolute maximum rating (Ta = 25 °C)

| Parameter | Symbol | Rating | Unit |
|---|------------------------------------|-----------|------|
| Continuous drain current V _{GS} =0v | I _{D(m)} | 0.3 | A |
| Drain-source Voltage | V _{DSS} | 400 | V |
| Gate-source Voltage | V _{GS} | ±10 | V |
| Operating junction and storage temperature range | T _j T _{STG} | -40to+150 | °C |

Pattern drawing



5. Electrical characteristics (Ta = 25 °C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--------------------------------------|----------------------|---|------|--------|------|------|
| Drain to source breakdown voltage | BV _{DSS} | V _{GS} = -5V I _D = 100uA | 400 | | | V |
| Gate to source off voltage | V _{GS(off)} | V _{DS} = 25V I _{DS} = 10uA | -1.8 | -2.3 | -3.5 | V |
| Gate to source leakage current | I _{GSS} | V _{GS} = ±10V V _{DS} = 0V | | ± 0.07 | ± 1 | μA |
| Drain to source leakage current | I _{D(OFF)} | V _{GS} = -5V V _{DS} = 400V | | | 1 | μA |
| Drain to source on resistance | R _{DS(on)} | V _{GS} = 0V I _D = 120mA | | 14 | 25 | Ω |
| Diode forward voltage drop | V _{SD} | V _{GS} = -10V I _{SD} = 120mA | | 0.84 | 1.8 | V |

